

ABSTRACT OF THE DISCLOSURE

A semiconductor processing method includes forming an antireflective coating comprising Ge and Se over a substrate to be patterned. Photoresist is formed over the antireflective coating. The photoresist is exposed to actinic radiation effective to pattern the photoresist. The antireflective coating reduces reflection of actinic radiation during the exposing than would otherwise occur under identical conditions in the absence of the antireflective coating. After the exposing, the substrate is patterned through openings in the photoresist and the antireflective coating using the photoresist and the antireflective coating as a mask. In one implementation, after patterning the substrate, the photoresist and the antireflective coating are chemically etched substantially completely from the substrate using a single etching chemistry.